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APPLICANT : NIKKO KYODO CO LTD;

INVENTOR : SAKASHITA YUKIO;

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TITLE : FORMATION OF ORIENTED TA₂O₅ THIN FILM

ABSTRACT : PURPOSE: To obtain the dense, homogeneous and highly oriented thin film low in impurities by oxidizing a specified raw gas introduced into a reactor along with an inert carrier gas with an oxidizing agent so as to grow the thin film on a base plate by chemical vapor deposition, etc.

CONSTITUTION: A tantalum alkoxide or ≥ 1 kind among β -diketone-based metallic complexes are introduced as the gaseous raw material into a reactor along with an inert carrier gas such as argon. The gaseous raw material is oxidized by ≥ 1 kind of oxidizing agent among O₂, steam, nitrous oxide, etc., to form an oriented Ta₂O₅ thin film on the base plate of Si, etc., by plasma chemical vapor deposition(CVD), photo-CVD, etc.

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